

FIG. 1

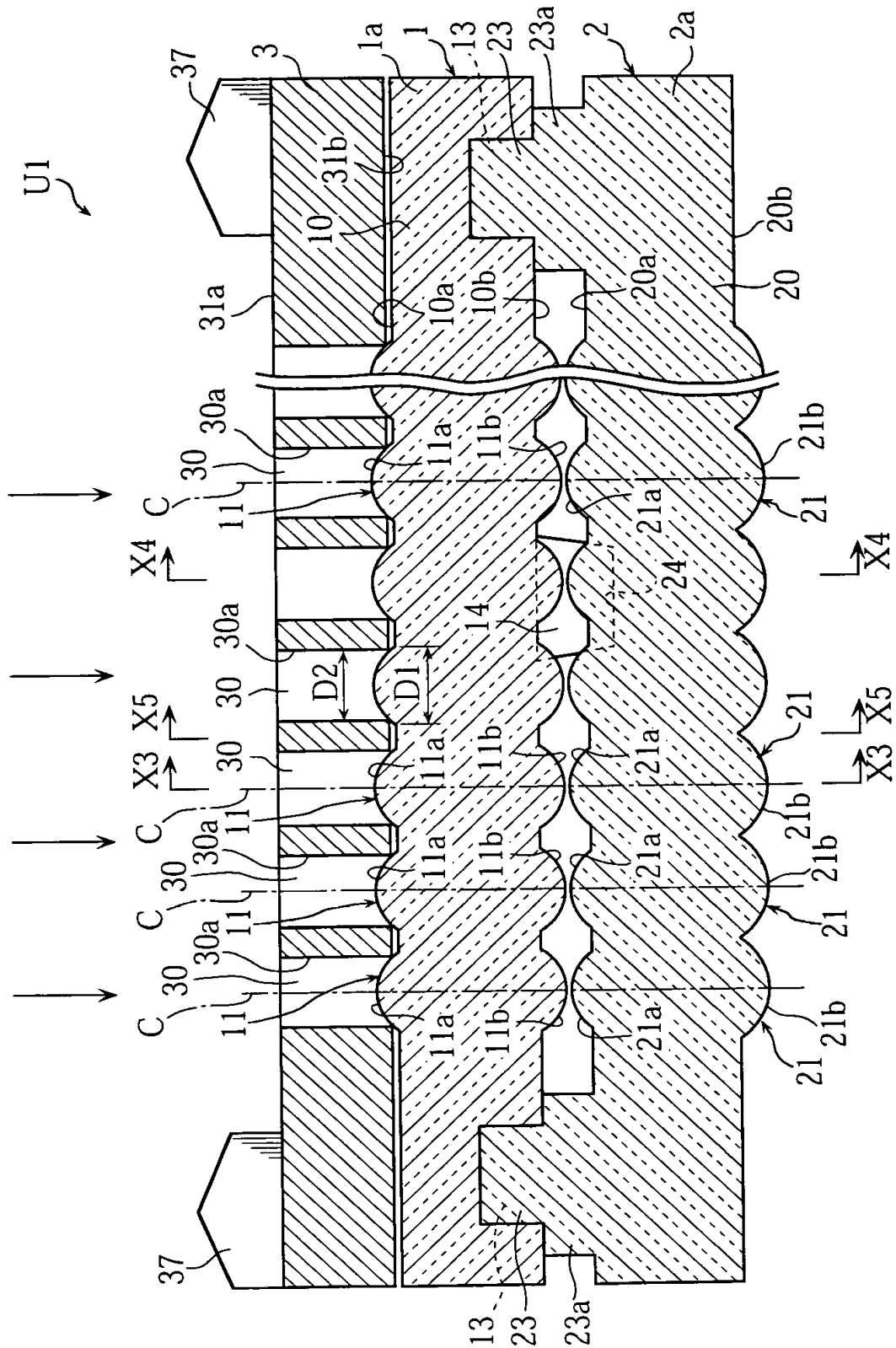


FIG.2

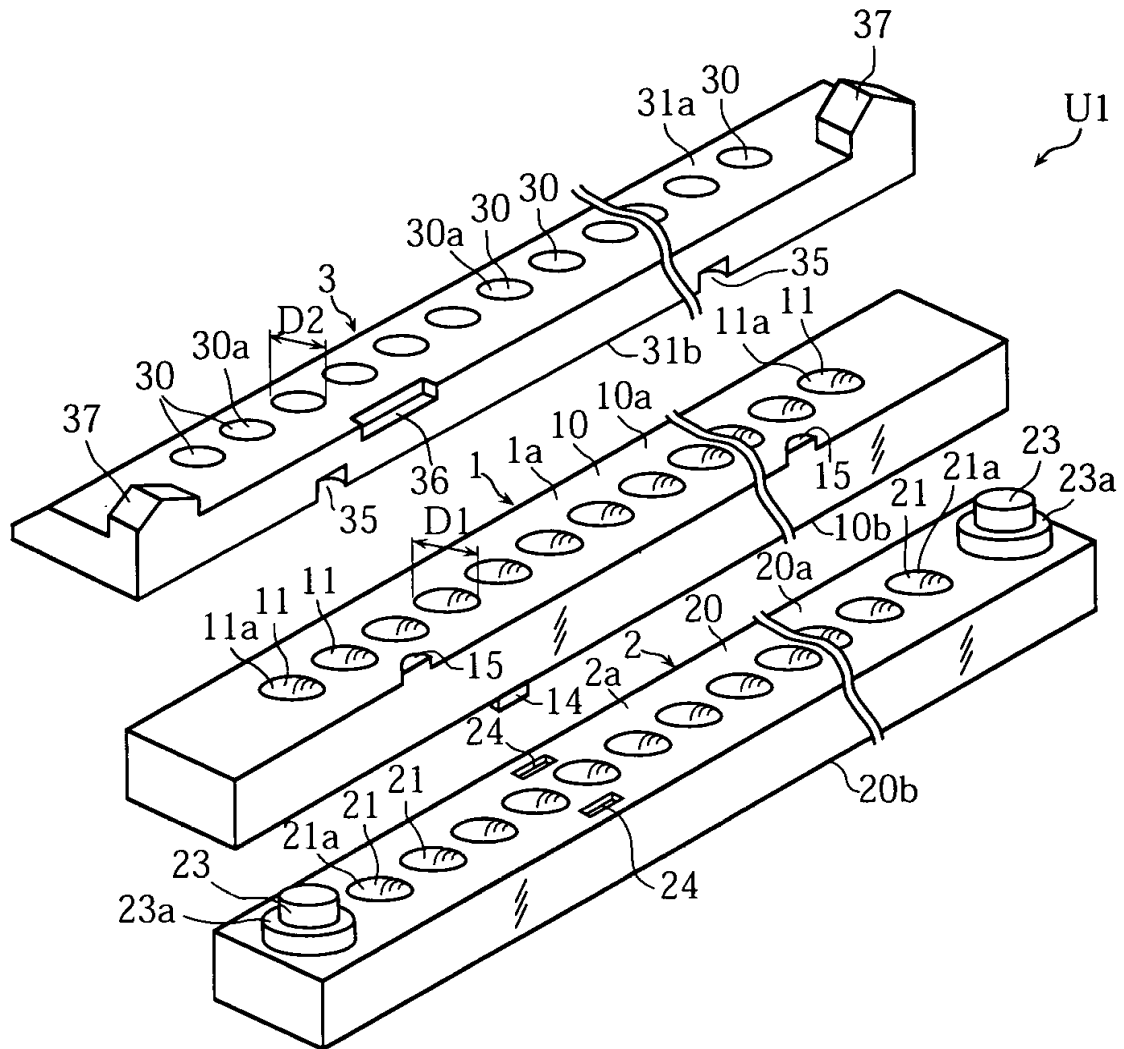


FIG.3

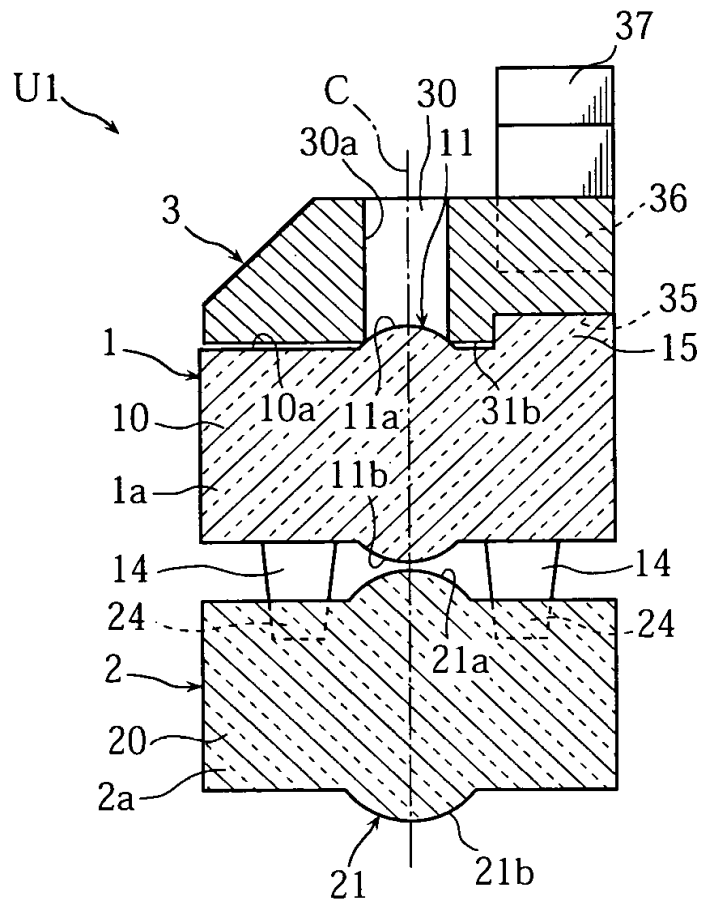


FIG.5

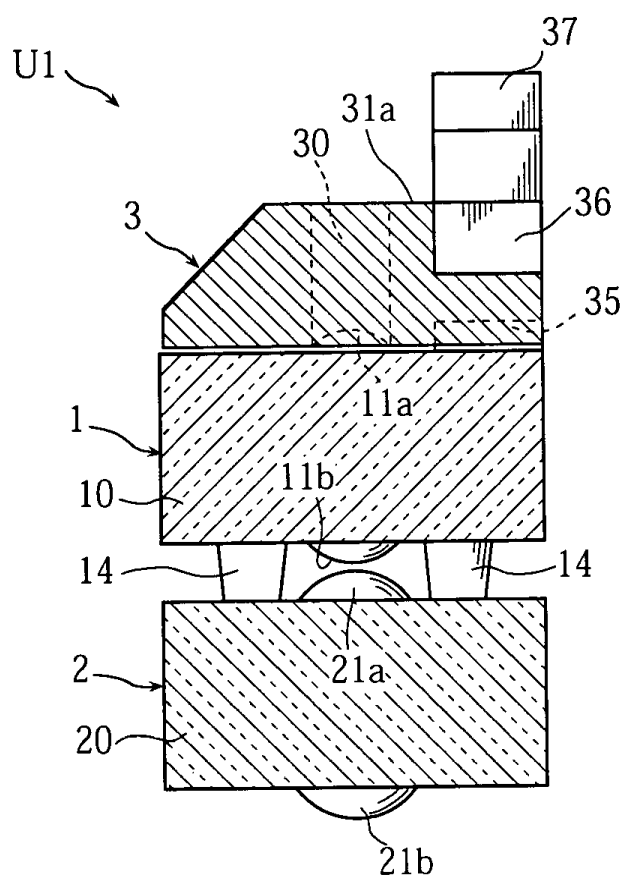


FIG.6

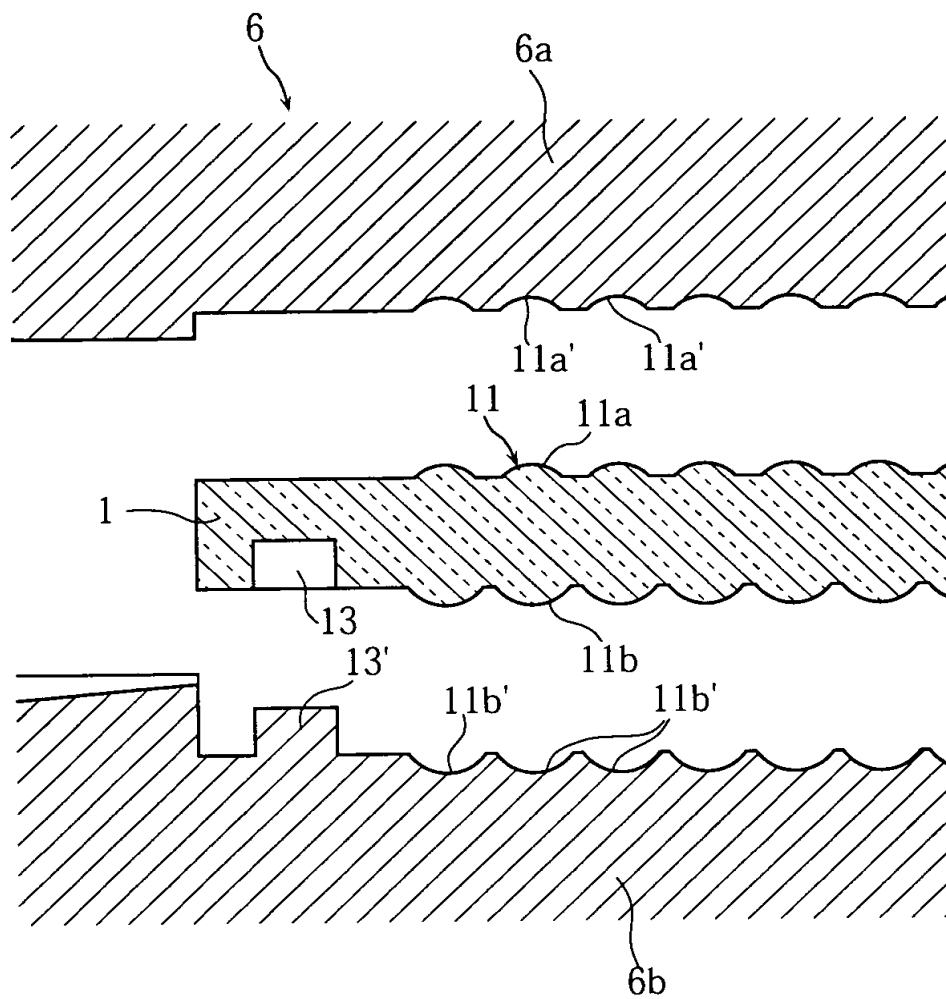


FIG. 7

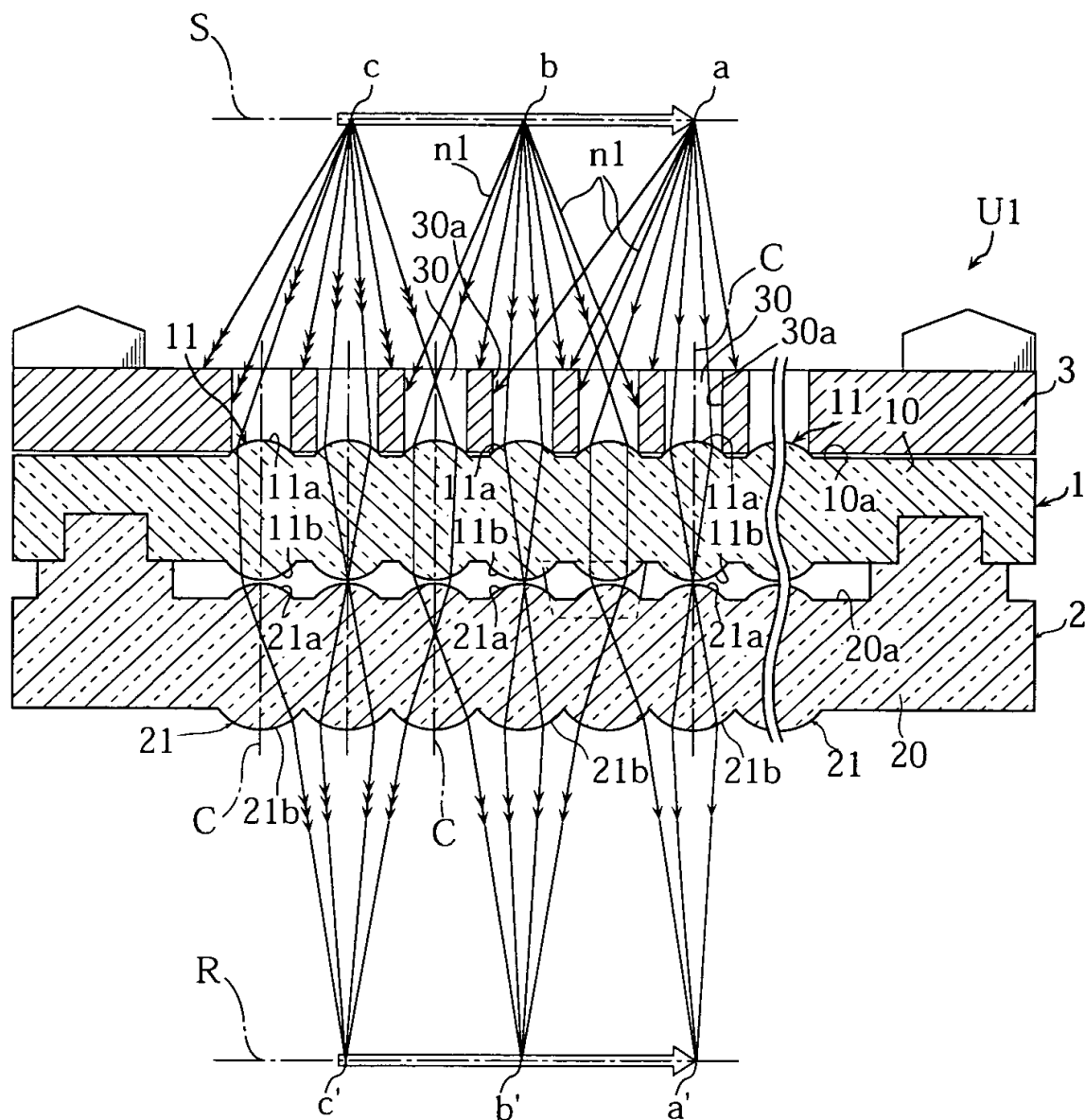


FIG. 9

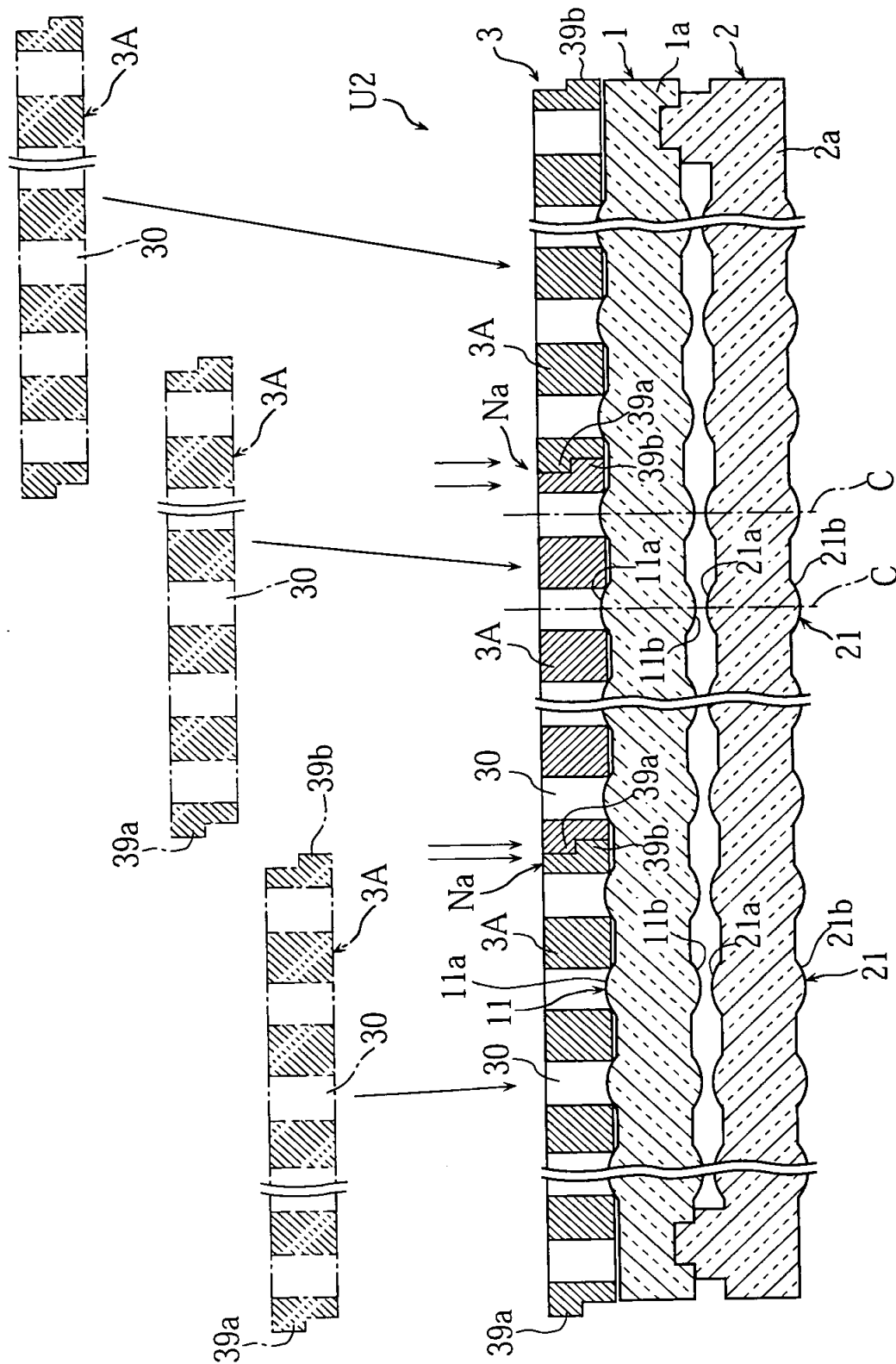


FIG.10

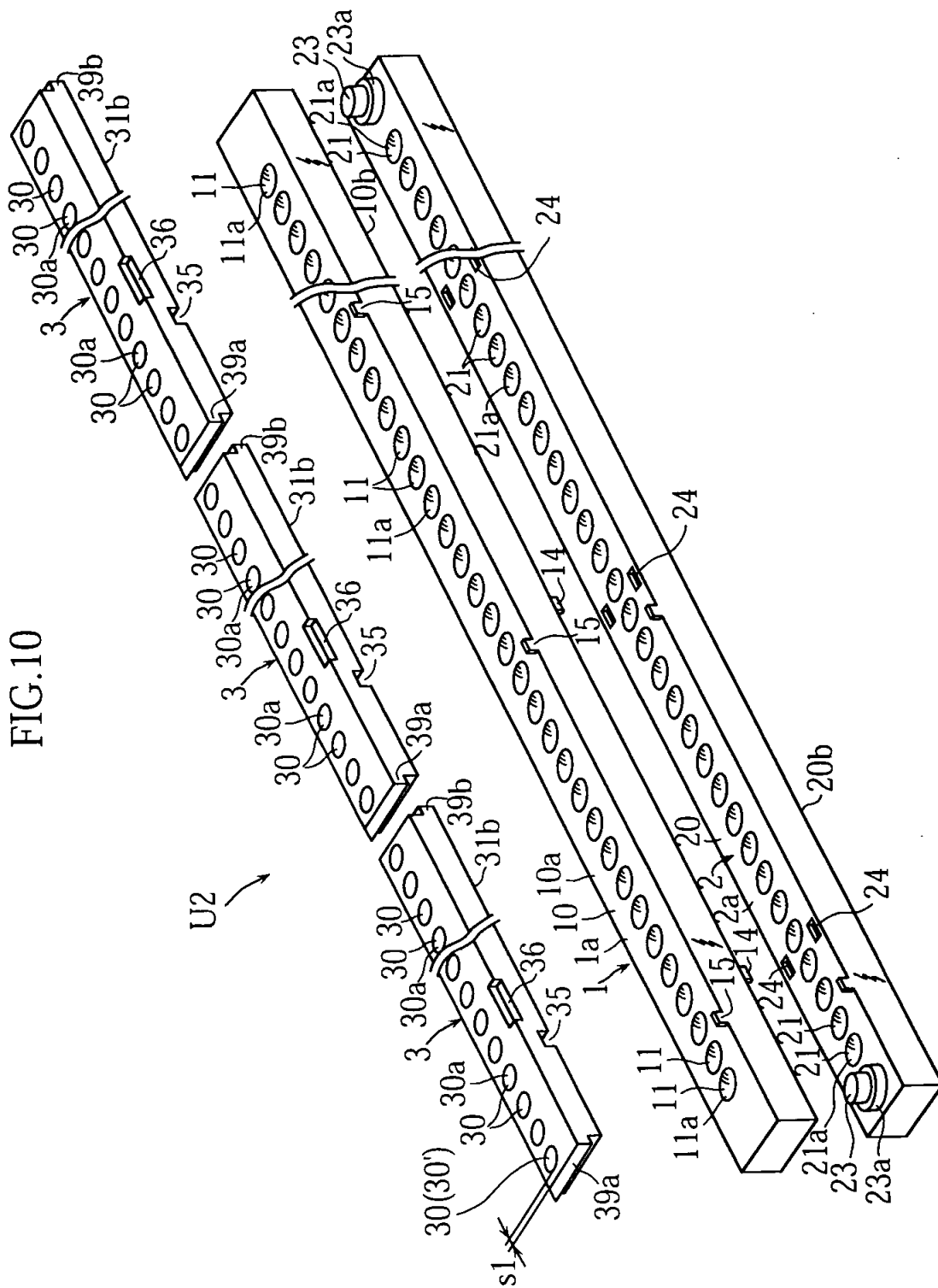


FIG.11

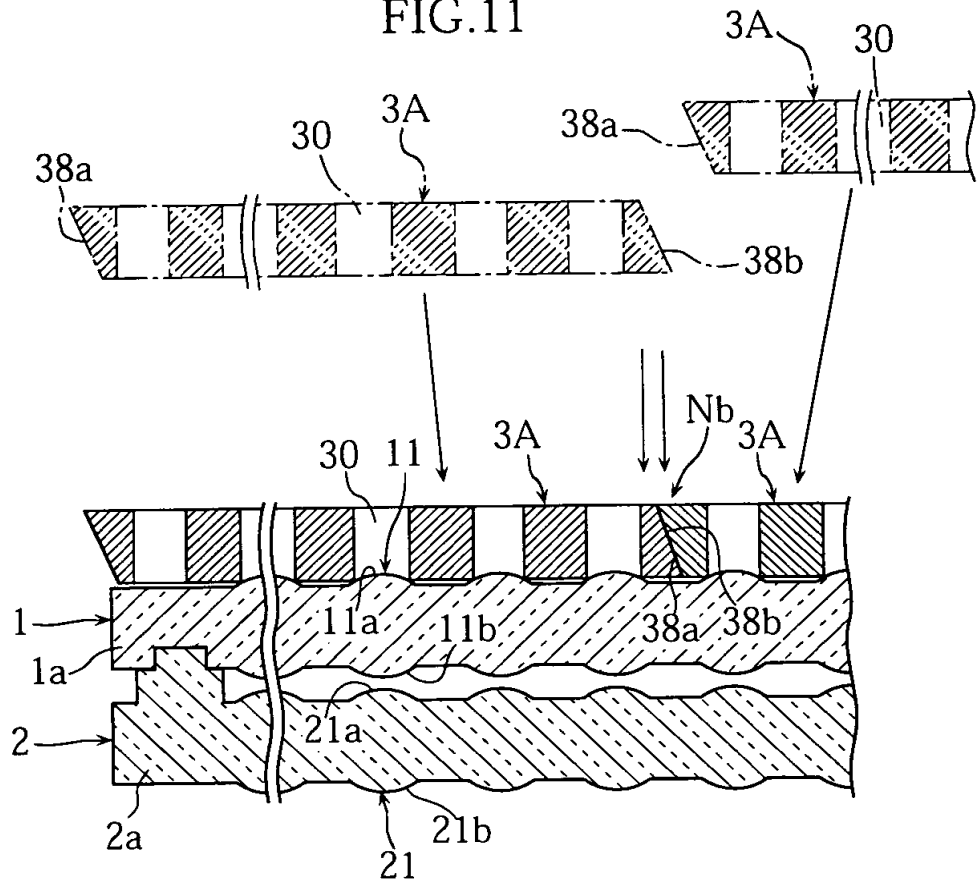


FIG.12A

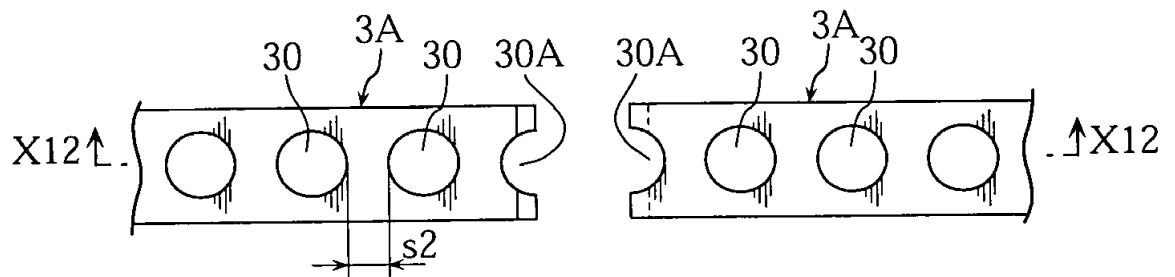
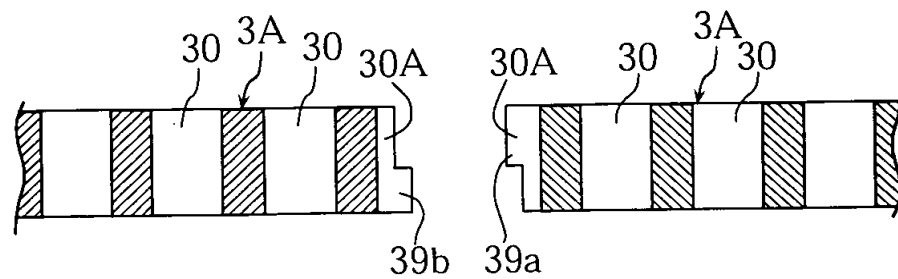


FIG.12B



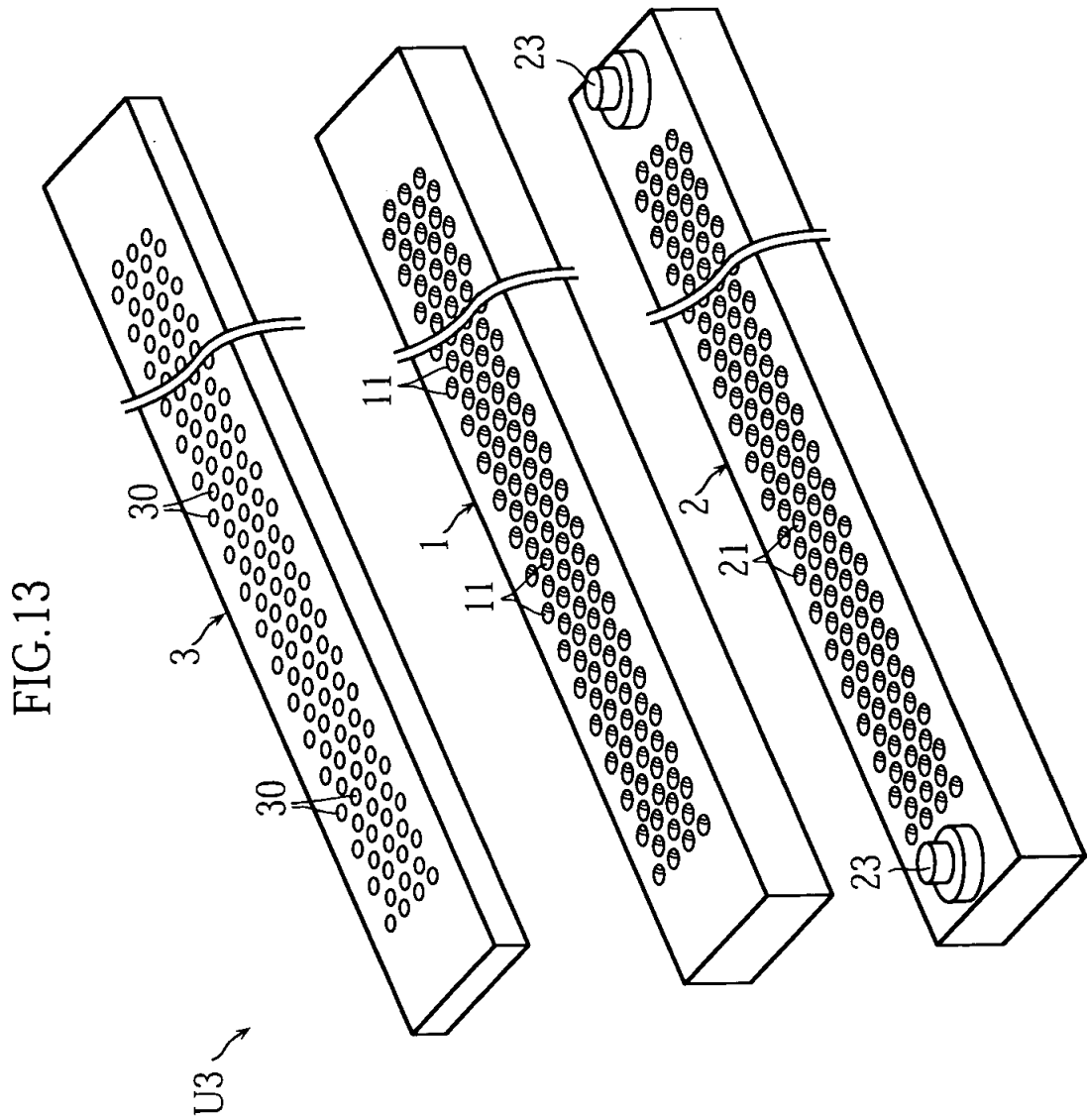


FIG.14

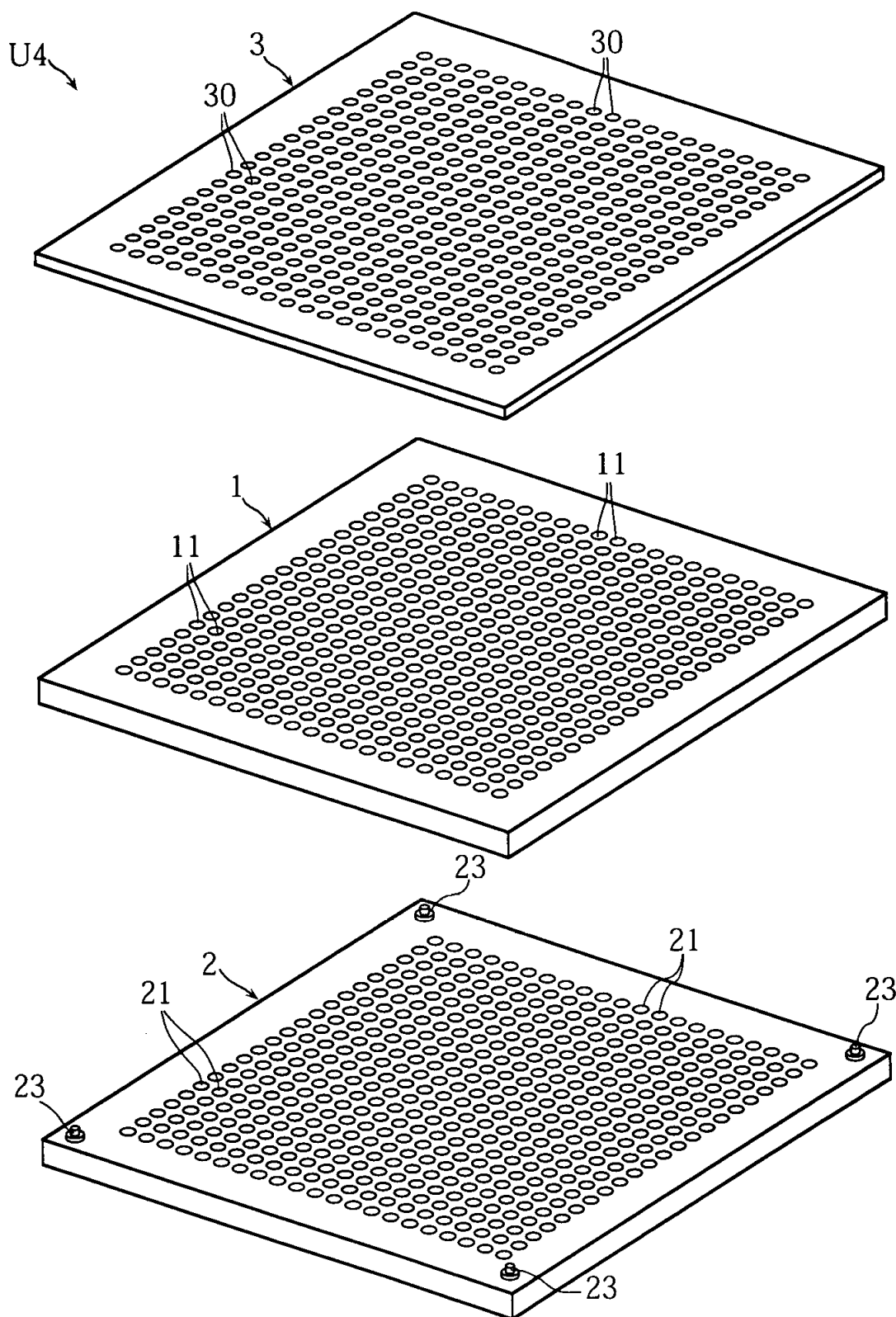


FIG.15

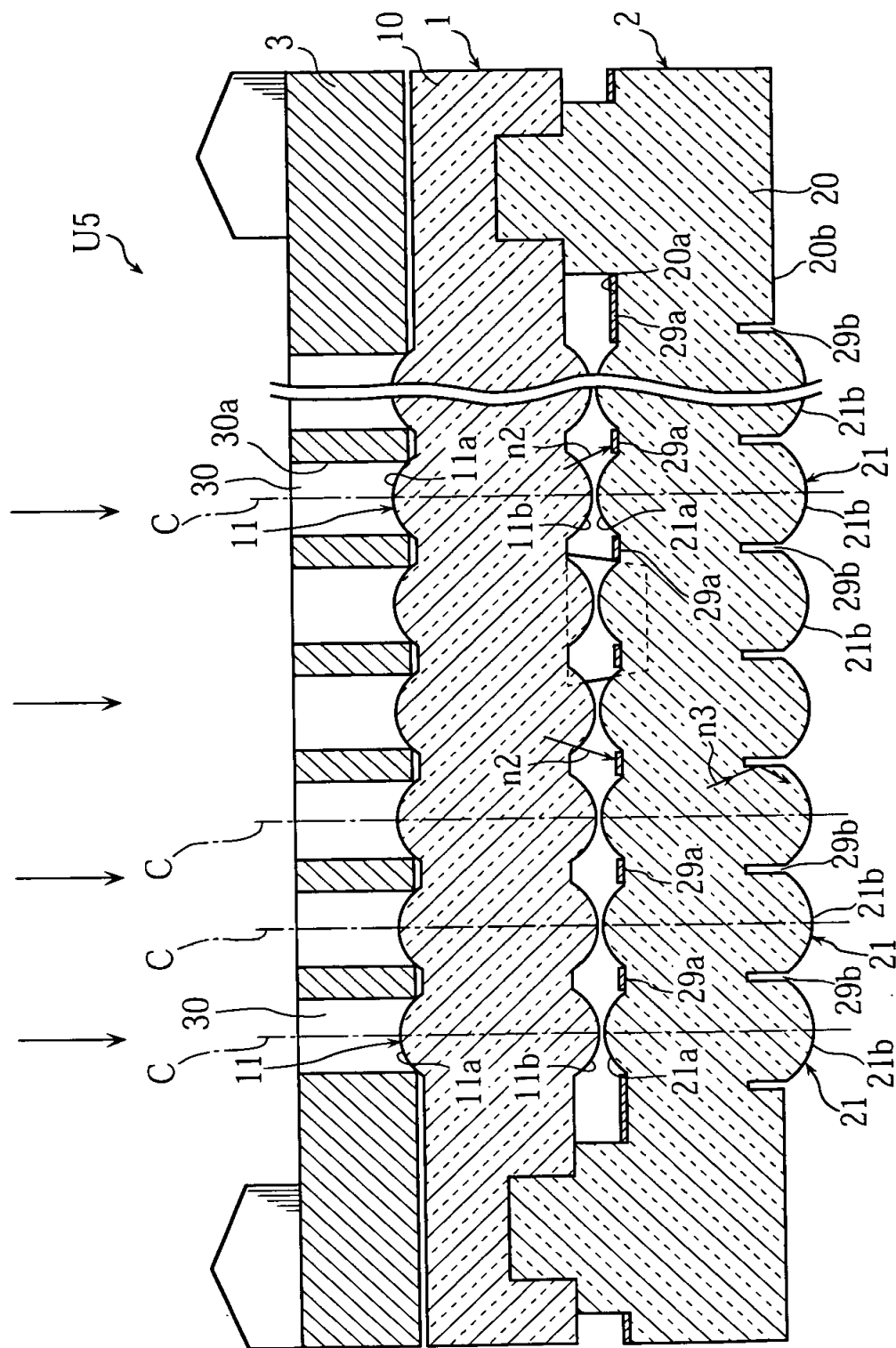


FIG.16

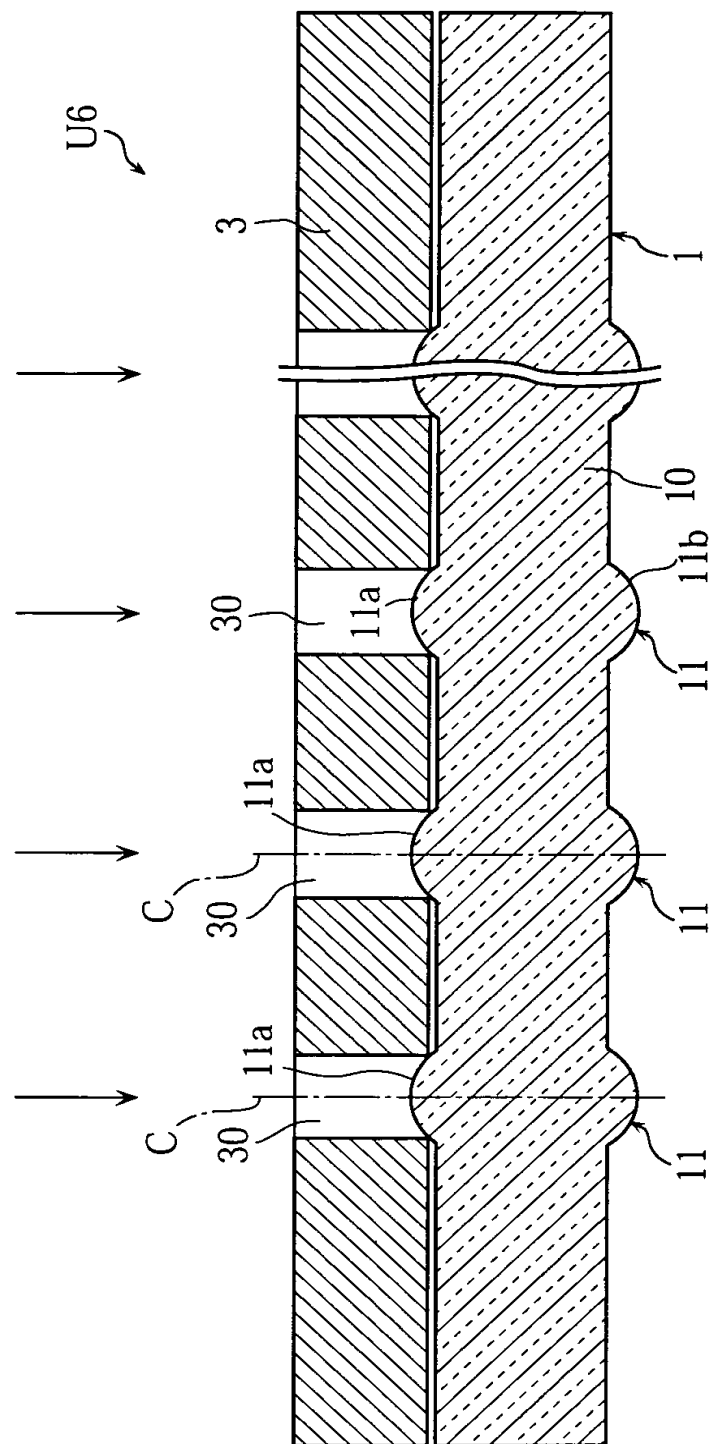


FIG.17

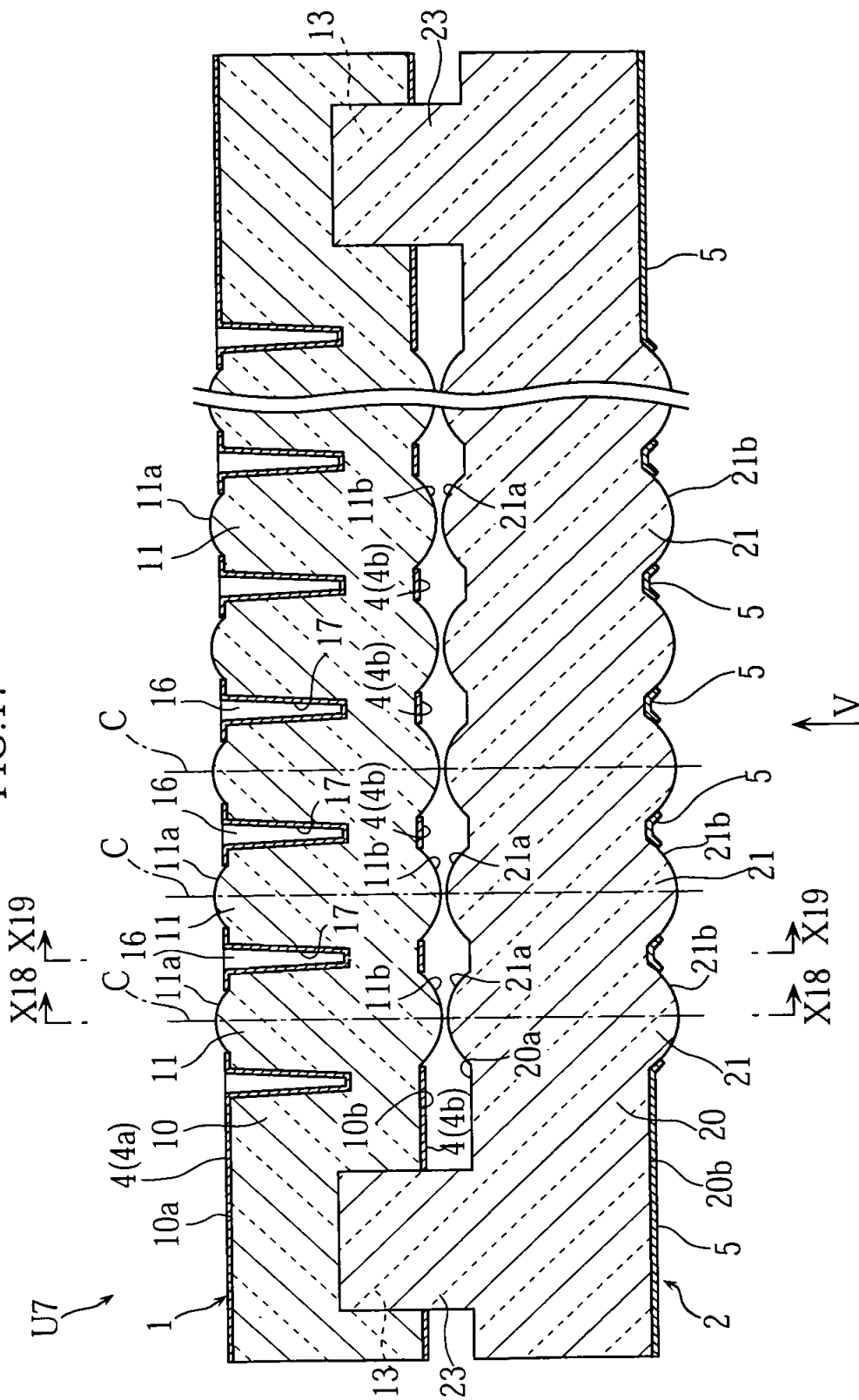


FIG.18

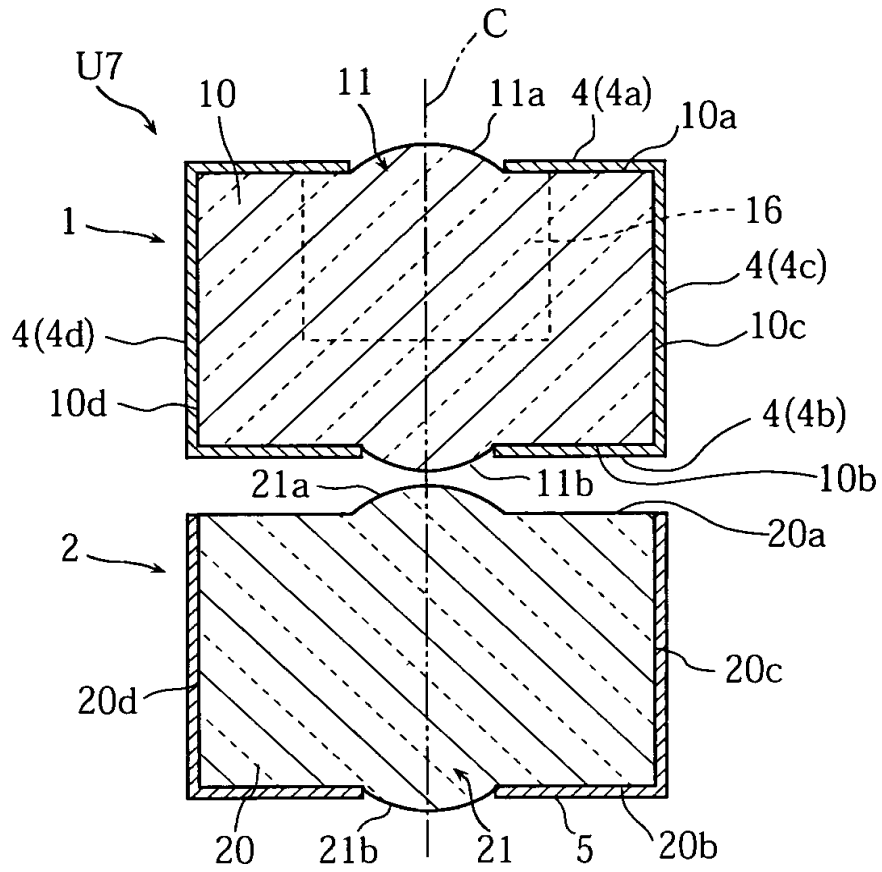


FIG.19

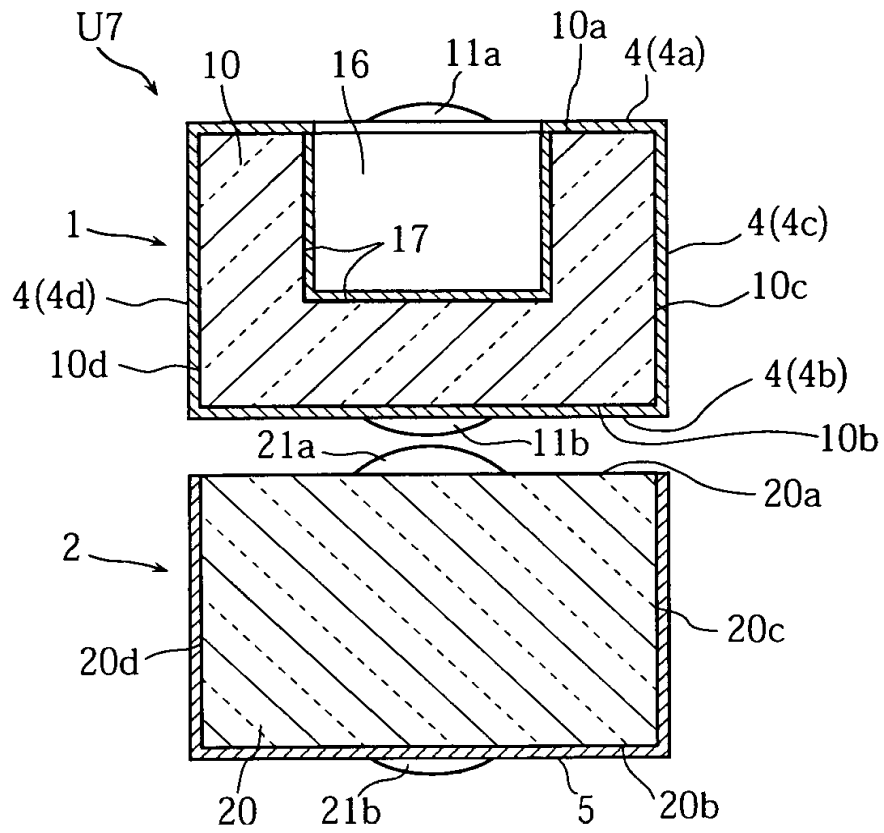
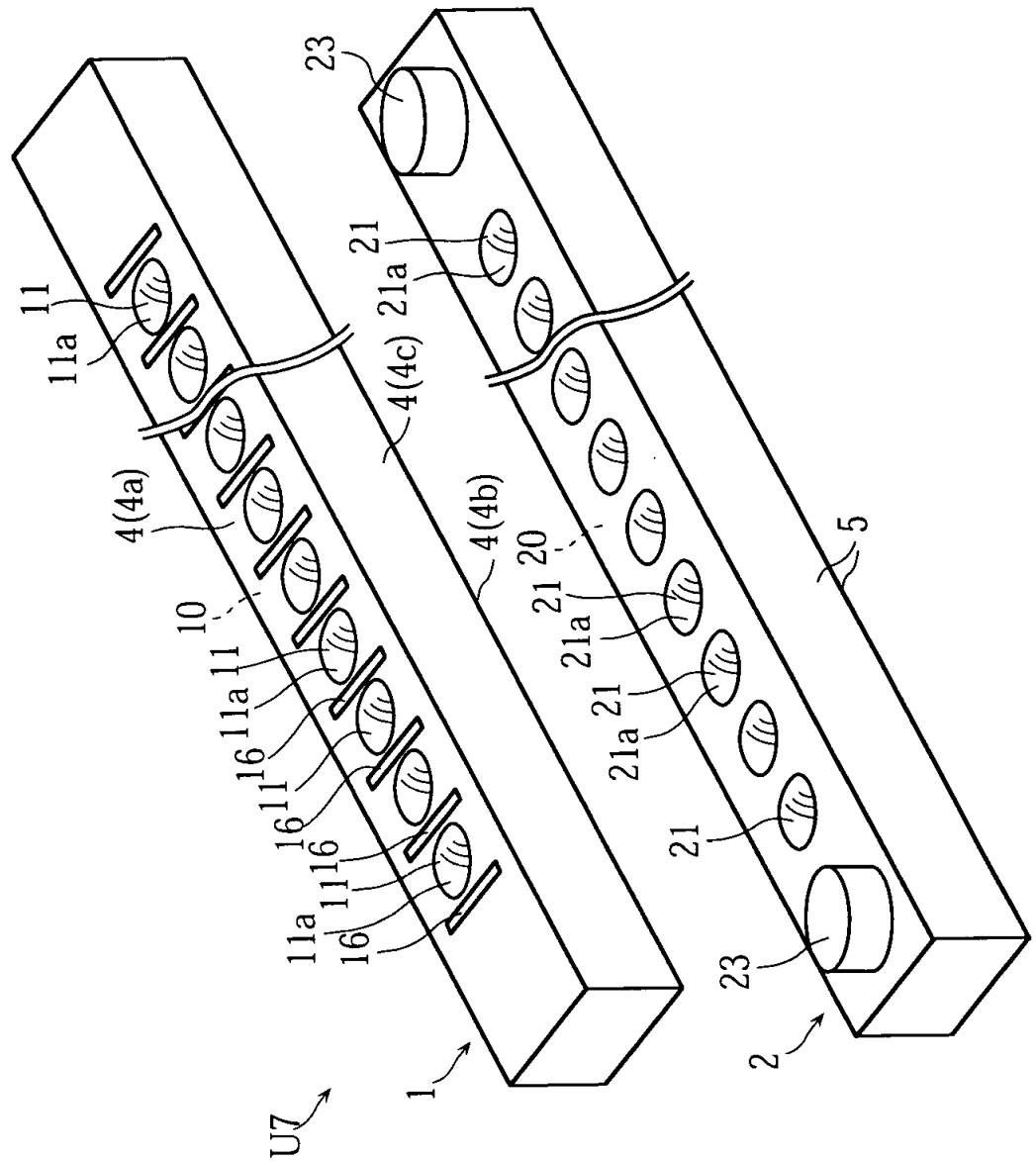


FIG.20



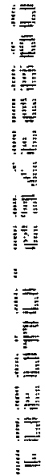
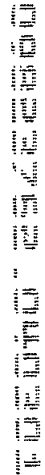
[illegible][illegible]

FIG.23

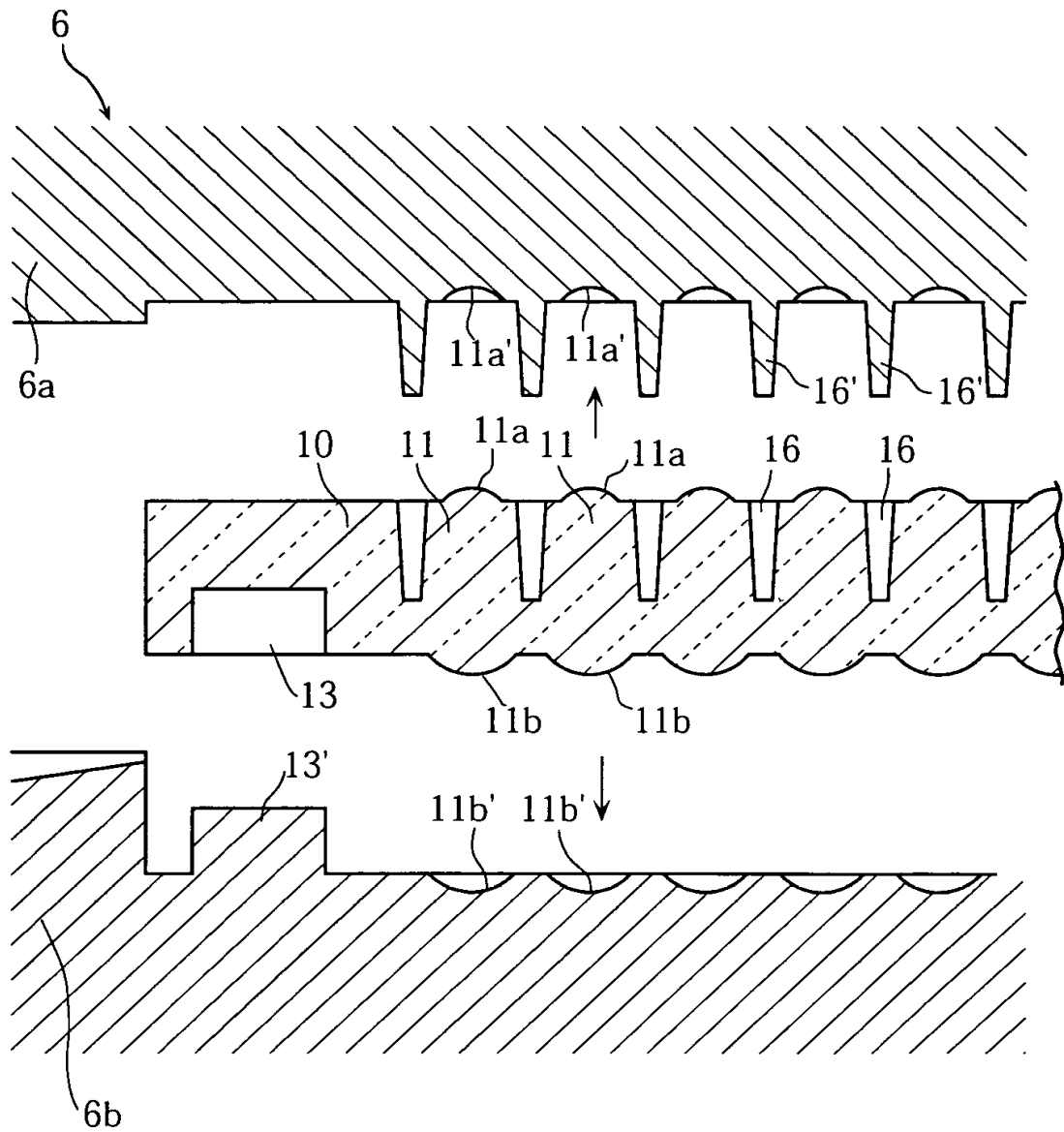


FIG.24

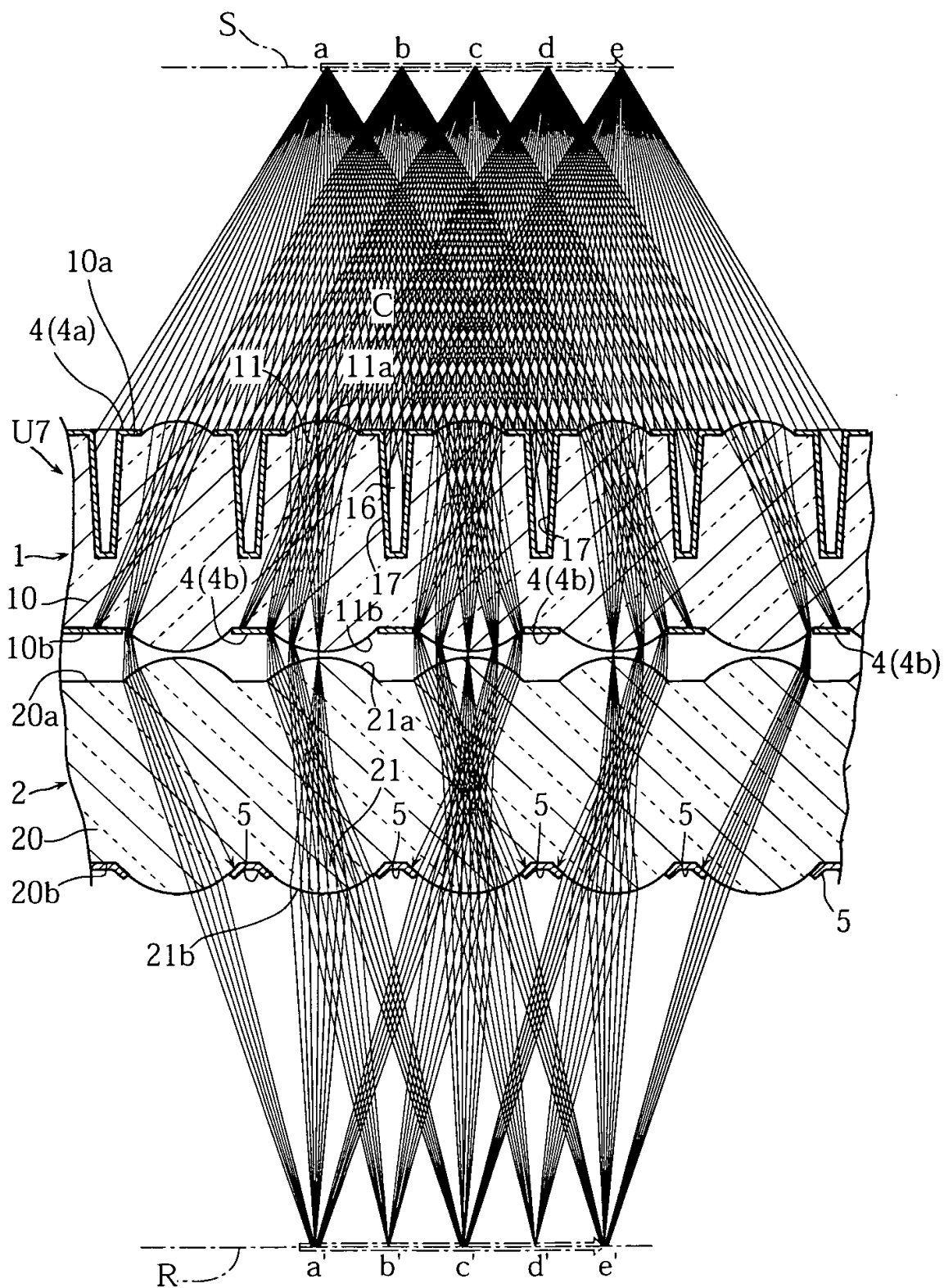
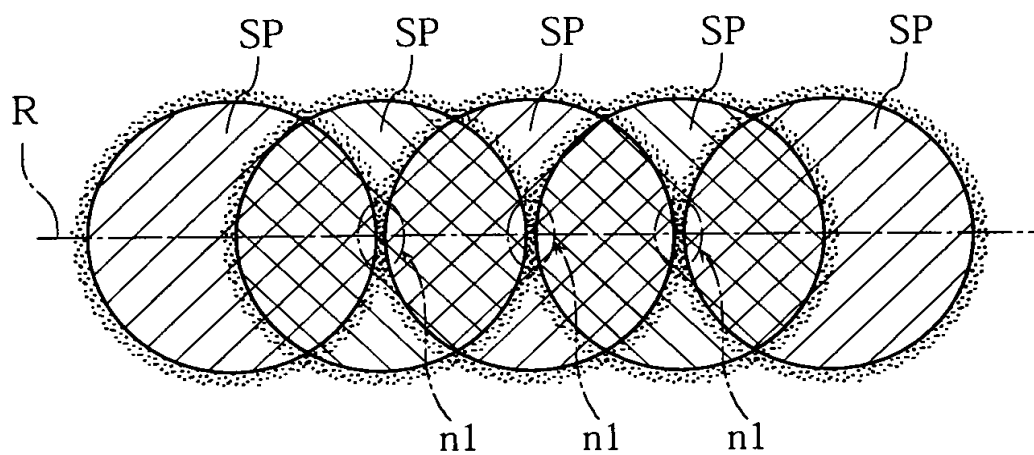


FIG.25



A detailed cross-sectional diagram of a semiconductor device. A large sphere labeled 77 is positioned above a horizontal layer 70. An arrow labeled G points towards the sphere, and another arrow labeled La points from the sphere down to a contact point on layer 70. Below layer 70 is a substrate 71 containing various layers and structures. Arrows indicate light paths or signal flow through several components: 10, 11, 1, U7, 75, 2, 21, and 20. Specific features are labeled 11a, 21a, 11b, and 21b. At the bottom, there are two small rectangular components labeled 73 and 74, separated by a gap 72. A dashed line labeled -78- indicates a boundary or interface within the substrate.

FIG. 27

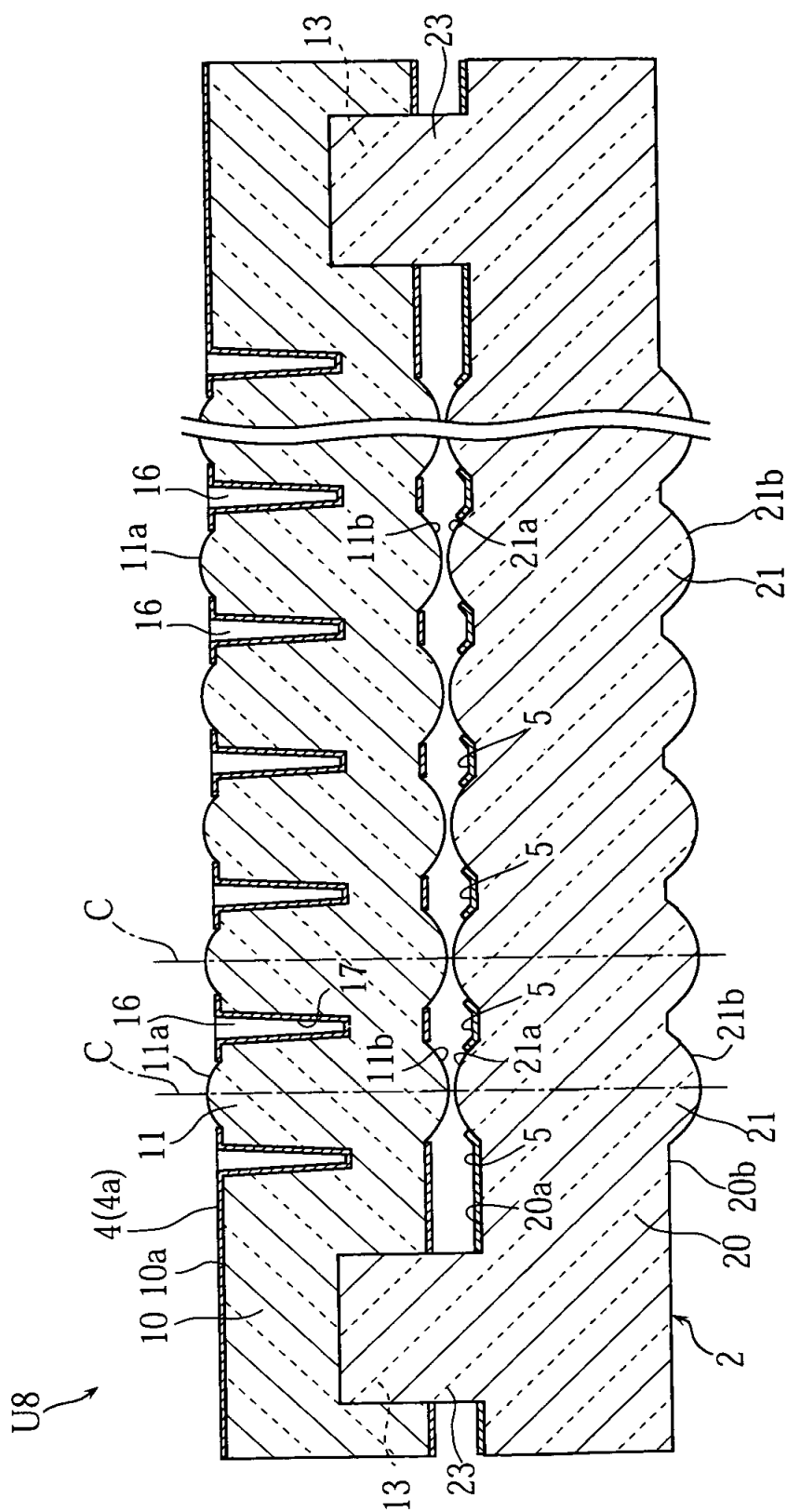


FIG.28

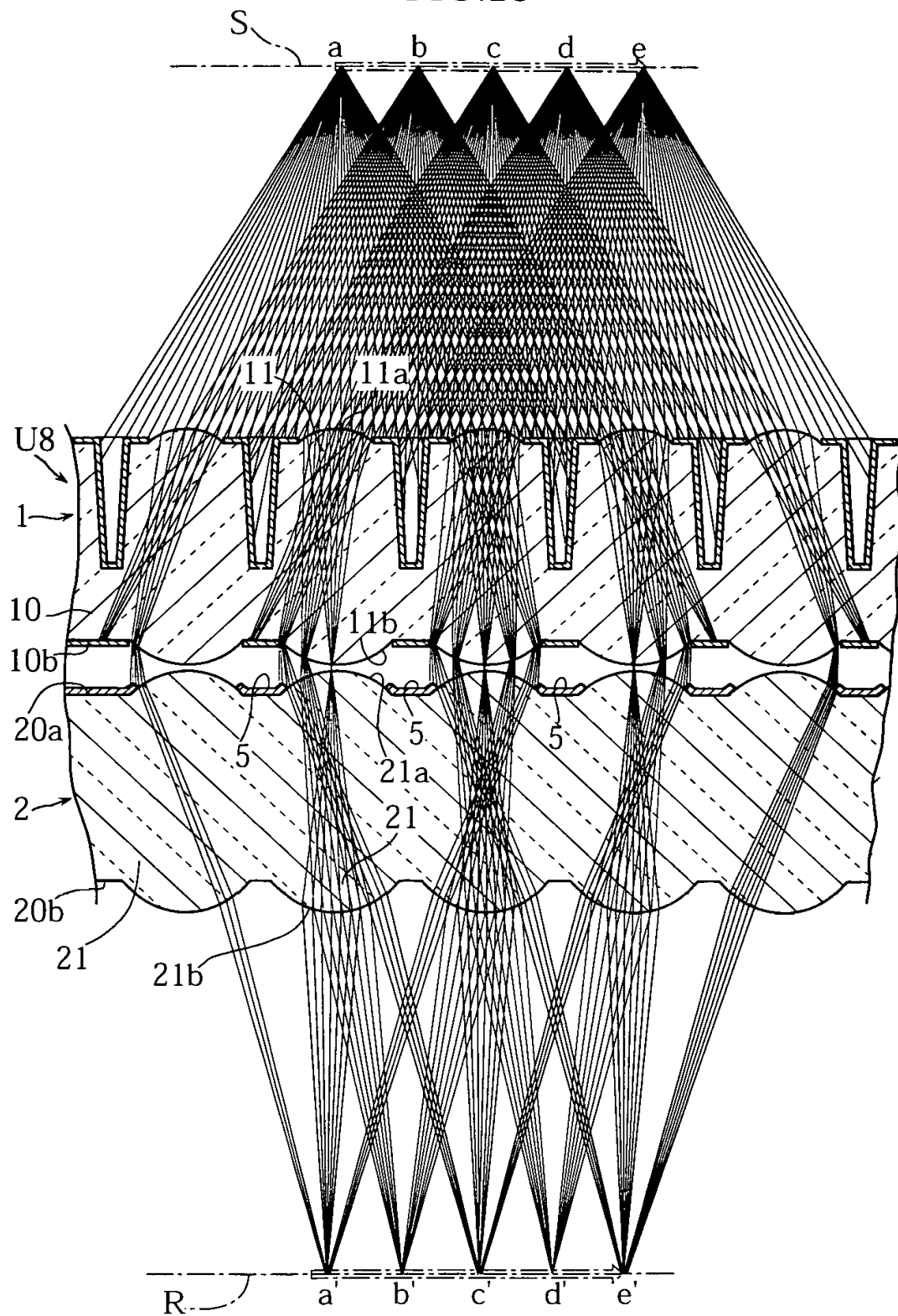


FIG.29
PRIOR ART

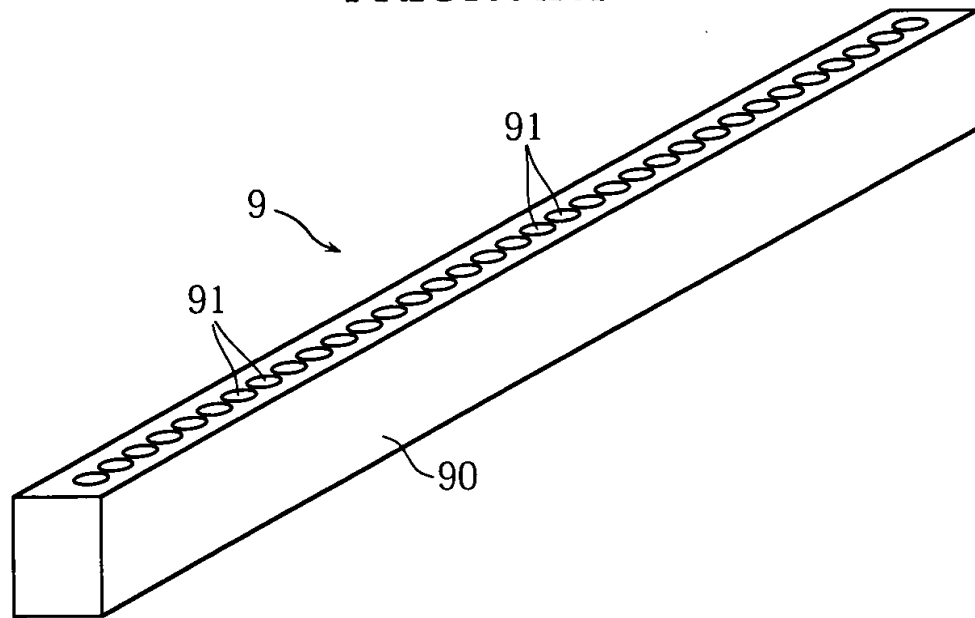


FIG.30
PRIOR ART

